

600V 60A FieldStop Trench IGBT

Description

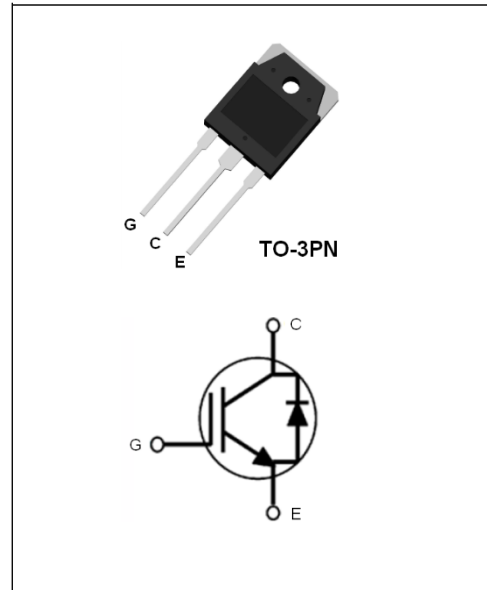
The device is designed by advanced FieldStop Trench technology process. This IGBT offer low $V_{CE(sat)}$, high speed switching performance and excellent quality for application such as PFC,UPS, Welder, PV Inverter and other switching applications.

Features

- FieldStop Trench Technology, Positive temperature coefficient
- $V_{CE(sat)}=1.9V@I_C=60A$
- $t_{rr}=45ns$ (MAX.)
- High Speed Switching & Low Power Loss
- High Input Impedance

Applications

- PFC, UPS, Welder, PV Inverter



Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit	
V_{CES}	Collector to Emitter Voltage	600	V	
V_{GES}	Gate to Emitter Voltage	± 20	V	
I_C	Collector Current	$T_C=25^\circ C$	100	A
		$T_C=100^\circ C$	60	A
I_{CM}	Pulsed Collector Current	180	A	
I_F	Diode Continuous Forward Current	$T_C=100^\circ C$	15	A
I_{FM}	Diode Maximum Forward Current	90	A	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$	416	W
		$T_C=100^\circ C$	214	W
T_J	Operating Junction Temperature Range	-40~+175	$^\circ C$	
T_{STG}	Storage Temperature Range	-55~+150	$^\circ C$	

Thermal Characteristics

Symbol	Parameter	Ratings	Unit
$R_{th(J-C)}$ (IGBT)	Thermal Resistance, Junction to case for IGBT	0.3	$^\circ C/W$
$R_{th(J-C)}$ (Diode)	Thermal Resistance, Junction to case for Diode	1.2	$^\circ C/W$
$R_{th(J-A)}$	Thermal Resistance, Junction to Ambient	40	$^\circ C/W$

Electrical Characteristics of IGBT @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE}=0V, I_C=250\mu A$	600	-	-	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=60A, V_{GE}=15V$	-	1.9	2.2	V
		$I_C=60A, V_{GE}=15V, T_C=125\text{ }^\circ\text{C}$	-	2.2	-	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE}=V_{GE}, I_C=250\mu A$	4.0	4.6	6.0	V
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=V_{CES}, V_{GE}=0V$	-	-	5	μA
I_{GES}	Gate to Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0V$	-	-	± 250	nA

Electrical Characteristics of Diode @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=15A$	-	2.10	2.5	V
		$I_F=15A, T_C=125\text{ }^\circ\text{C}$	-	1.58	-	V
t_{rr}	Diode Reverse Recovery Time	$I_F=15A, di/dt=-200A/\mu s$	-	-	45	ns
I_{rr}	Diode Peak Reverse Recovery Current		-	2.4	-	A
Q_{rr}	Diode Reverse Recovery Charge		-	33	-	nC

Switching Characteristics @ $T_C=25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$t_{d(on)}$	Turn-on Delay Time	$I_C=60A, V_{CC}=600V, V_{GE}=15V, R_G=14\Omega, \text{Inductive Load, } T_C=25\text{ }^\circ\text{C}$	-	42	-	ns	
t_r	Rising Time		-	83	-	ns	
$t_{d(off)}$	Turn-off Delay Time		-	220	-	ns	
t_f	Falling Time		-	14	-	ns	
E_{on}	Turn-on Switching Loss		-	1.32	-	mJ	
E_{off}	Turn-off Switching Loss		-	0.86	-	mJ	
E_{ts}	Total Switching Loss		-	2.18	-	mJ	
$t_{d(on)}$	Turn-on Delay Time		$I_C=60A, V_{CC}=600V, V_{GE}=15V, R_G=14\Omega, \text{Inductive Load, } T_C=125\text{ }^\circ\text{C}$	-	38	-	ns
t_r	Rising Time			-	80	-	ns
$t_{d(off)}$	Turn-off Delay Time			-	230	-	ns
t_f	Falling Time	-		14	-	ns	
E_{on}	Turn-on Switching Loss	-		1.86	-	mJ	
E_{off}	Turn-off Switching Loss	-		0.82	-	mJ	
E_{ts}	Total Switching Loss	-		2.68	-	mJ	
C_{ies}	Input Capacitance	$V_{GE}=0V, V_{CE}=25V, f=1.0MHz$	-	2405	-	pF	
C_{res}	Reverse Transfer Capacitance		-	66	-	pF	
C_{oes}	Output Capacitance		-	289	-	pF	
Q_g	Total Gate Charge	$I_C=60A, V_{CE}=480V, V_{GE}=15V$	-	98	-	nC	
Q_{ge}	Gate to Emitter Charge		-	22	-	nC	
Q_{gc}	Gate to Collector Charge		-	50	-	nC	
t_{sc}	Short Circuit With stand Time	$V_{CC}=600V, V_{GE}=15V$	10	-	-	us	

Package Dimensions

TO-3PN

(Dimensions in Millimeters)

